

RJK4006DPD

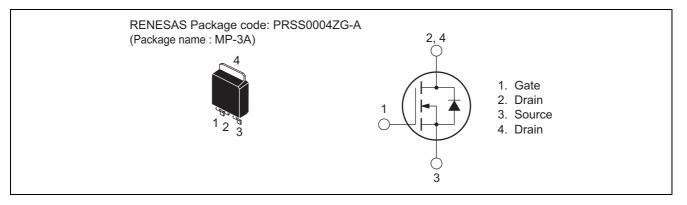
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1547-0100 Rev.1.00 Dec 19, 2008

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	400	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID ^{Note4}	8	А
Drain peak current	I _{D (pulse)} Note1	24	А
Body-drain diode reverse drain current	I _{DR}	8	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	24	А
Avalanche current	I _{AP} ^{Note3}	8	А
Avalanche energy	E _{AR} ^{Note3}	3.7	mJ
Channel dissipation	Pch ^{Note2}	65	W
Channel to case thermal impedance	θch-c	1.92	°C/W
Channel temperature	Tch	150	٥°
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25° C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

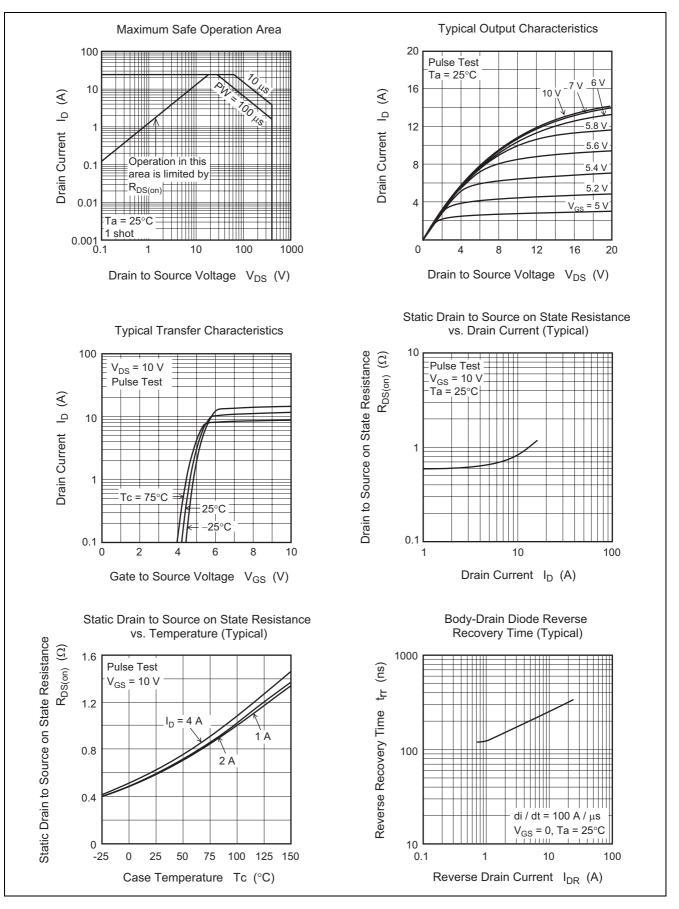
4. Limited by maximum safe operation area

Electrical Characteristics

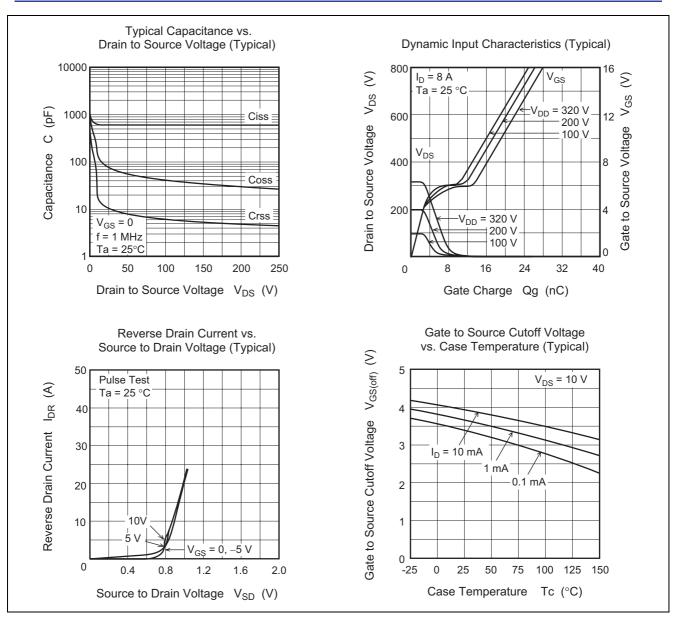
						$(Ta = 25^{\circ}C)$	
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	V _{(BR)DSS}	400		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 400 \text{ V}, V_{GS} = 0$	
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$	
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	
Static drain to source on state resistance	R _{DS(on)}	_	0.69	0.80	Ω	$I_D = 4$ A, $V_{GS} = 10$ V ^{Note5}	
Input capacitance	Ciss	_	620		pF	V _{DS} = 25 V	
Output capacitance	Coss	_	80		pF	V _{GS} = 0 f = 1 MHz	
Reverse transfer capacitance	Crss		11		pF		
Turn-on delay time	t _{d(on)}	_	30	—	ns	I _D = 4 A	
Rise time	tr	_	30	_	ns	$V_{GS} = 10 V$ $R_L = 50 \Omega$ $Rg = 10 \Omega$	
Turn-off delay time	t _{d(off)}	_	60	_	ns		
Fall time	t _f	_	20	_	ns		
Total gate charge	Qg	—	20	_	nC	V _{DD} = 320 V	
Gate to source charge	Qgs	_	4	_	nC	V _{GS} = 10 V	
Gate to drain charge	Qgd	—	9	_	nC	$I_D = 8 A$	
Body-drain diode forward voltage	V _{DF}	—	0.9	1.5	V	$I_F = 8 \text{ A}, V_{GS} = 0^{\text{Note5}}$	
Body-drain diode reverse recovery time	t _{rr}		230	—	ns	$I_F = 8 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$	

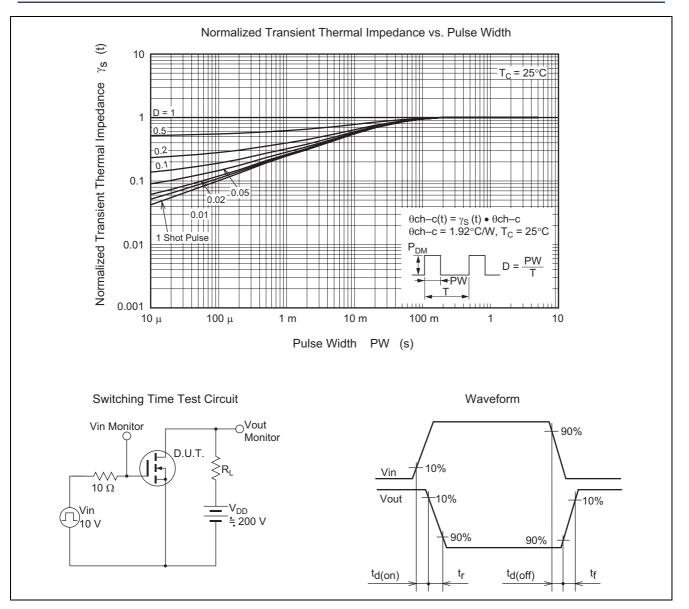
Notes: 5. Pulse test

Main Characteristics



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Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
Package Name MP-3A	SC-63	PRSS0004ZG-A	_	0.32g	Onit. Init
		0.76 ± 0.2	3.6 ± 0.2 ± 0.2 ± 0.2 ± 0.7 ± 0	$\begin{array}{c} 2.3 \\ 0.5 \pm 0.2 \\ 0.1 \pm 0.1 \\ 0.5 \pm 0.2 \\ 0.5 \pm 0.2 \\ \end{array}$	

Ordering Information

Part No.	Quantity	Shipping Container
RJK4006DPD-00-J2	3000 pcs	Taping

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